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<<非晶形半导体物理学PHYSICS OF>>

图书基本信息

书名：<<非晶形半导体物理学PHYSICS OF AMORPHOUS SEMICONDUCTORS>>

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内容概要

This is a useful textbook for graduate students in the fields of solid state physics and chemistry as well as electronic engineering. Presenting the fundamentals of amorphous semiconductors dearly, it will be essential reading for young scientists intending to develop new pre-paration techniques for more ideal amorphous semiconductors e.g.a-Si:H, to fabricate stable and efficient solar cells and thin film tran-sistors and new artificial amorphous materiats such as multilayers forquantum devices.　A large portion is devoted to the latest developments of amorphous semiconductors including electronic properties of a-Si:H, nature of weak bonds and gap states in a-Si:H, mechanisms for light-induced defect creation in a-Si:H and chalcogenides, and quantum phenomena in multilayer firms.

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